## PATENT ABSTRACTS OF JAPAN

(11)Publication numb r:

05-206036

(43)Dat of publication of application: 13.08.1993

(51)Int.CI.

H01L 21/205 // H01L 21/20

(21)Application number: 04-014991

(2.)

(71)Applicant: RIKAGAKU KENKYUSHO

(22)Date of filing:

30.01.1992

(72)Inventor: AOYANAGI KATSUNOBU

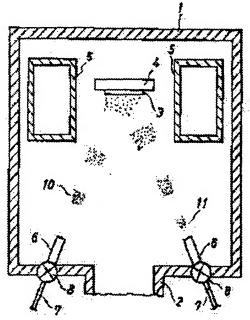
OZASA KAZUNARI MEGURO TAKASHI

## (54) FILM FORMATION METHOD AND FILM FORMATION APPARATUS

## (57)Abstract:

PURPOSE: To make it possible to from a thin film having an excellent in-plane uniformity, ALE condition, crystal quality, acute steepness of heterointerface, and others without damaging a substrate.

CONSTITUTION: A substrate 3 is arranged in a vacuum chamber 1 which is evacuated at a given degree of vacuum and heated. At the same time, with a gas ejection mechanism having a nozzle 6 arranged toward the substrate 3, and a high-speed switching valve 8 which provided near the nozzle 6, a material gas is ejected to the substrate 3 intermittently or continuously to grow crystals on the surface of the substrate 3 for the formation of a film.



## **LEGAL STATUS**

[Date of request for examination]

29.01.1999

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

3126787

[Date of registration]

02.11.2000

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of r j ction]

[Date of extinction of right]